

Amendments to the Claims:

Please cancel Claims 1 and 2.

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claim 1 (canceled)

Claim 2 (canceled)

Claim 3 (original): A fabrication method, comprising the steps of:

- a) implanting first dopant atoms into a semiconductor body to create a first-conductivity-type well diffusion therein; and
- b) implanting second dopant atoms into said semiconductor body, with more than twice the stopping distance and less than one-quarter of the dosage per unit area as said step a), to compensate atoms which channeled during said step a).